

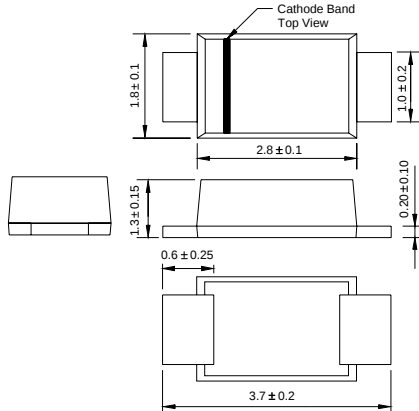


S1A THRU S1M

SURFACE MOUNT GENERAL PURPOSE SILICON RECTIFIER

Reverse Voltage - 50 to 1000 Volts Forward Current - 1.0 Ampere

SOD-123FL



Dimensions in millimeters

FEATURES

- ◆ Glass passivated device
- ◆ Ideal for surface mounted applications
- ◆ Low reverse leakage
- ◆ Metallurgically bonded construction
- ◆ High temperature soldering guaranteed:
250°C/10 seconds, 0.375" (9.5mm) lead length,
5 lbs. (2.3kg) tension

MECHANICAL DATA

Case: JEDEC SOD-123FL molded plastic body over passivated chip

Terminals: Plated axial leads, solderable per MIL-STD-750, Method 2026

Polarity: Color band denotes cathode end

Mounting Position: Any

Weight: 0.0007 ounce, 0.02 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

	SYMBOLS	S1A	S1B	S1D	S1G	S1J	S1K	S1M	UNITS
	MARK	S1A	S1B	S1D	S1G	S1J	S1K	S1M	
Maximum repetitive peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	VOLTS
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	VOLTS
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	VOLTS
Maximum average forward rectified current at $T_A=65^\circ\text{C}$ (NOTE 1)	$I_{(AV)}$	1.0							Amp
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method) $T_L=25^\circ\text{C}$	I_{FSM}	20.0							Amps
Maximum instantaneous forward voltage at 1.0A	V_F	1.1							Volts
Maximum DC reverse current $T_A=25^\circ\text{C}$ at rated DC blocking voltage $T_A=125^\circ\text{C}$	I_R	5.0 50.0							μA
Typical junction capacitance (NOTE 2)	C_J	4							pF
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$	180							K/W
Operating junction and storage temperature range	T_J, T_{STG}	-55 to +150							$^\circ\text{C}$

Note: 1. Averaged over any 20ms period.

2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

3. Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted



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FIG.1 – TYPICAL FORWARD CHARACTERISTIC

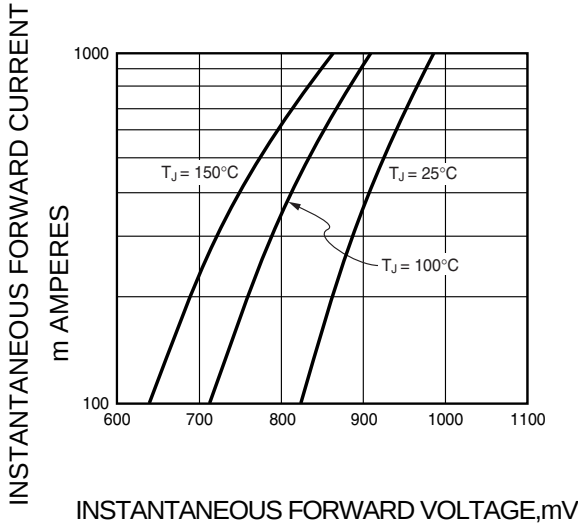


FIG.2 – TYPICAL JUNCTION CAPACITANCE

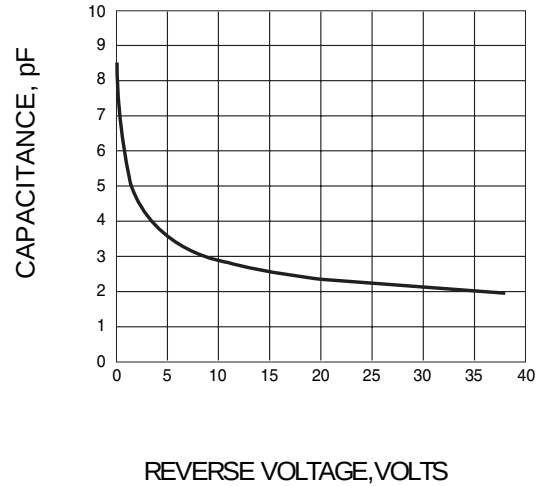


FIG.3 – TYPICAL INSTANTANEOUS REVERSE CHARACTERISTICS

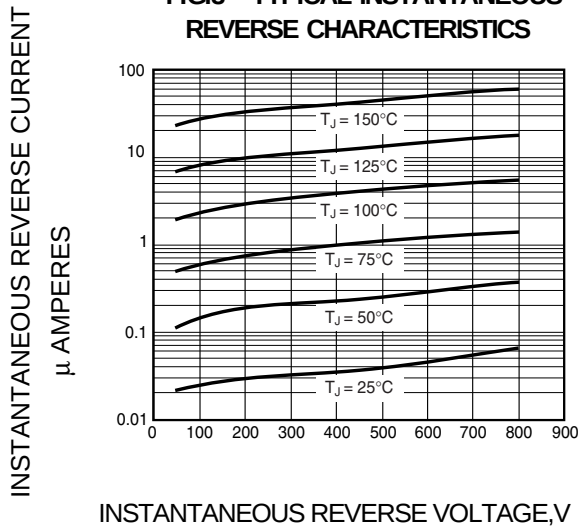


FIG.4 – FORWARD DERATING CURVE

